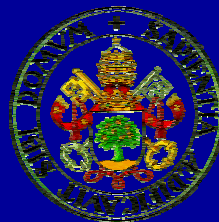


Atomistic Process Modeling

An Accurate and Straightforward
Approach for Complex
Processing Scenarios

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Thanks to:

P. Castrillo, R. Pinacho, L. Pelaz, J. Barbolla
University of Valladolid, Spain

George Gilmer, Conor Rafferty
Bell Labs Lucent Tech., USA

Outline

- The Problem: Complex Processing
- The Solution: Atomistic Kinetic Monte Carlo
- The Challenge: Obtaining the Parameters
- Looking Forward: Genetic Algorithms, Neural Networks, ...

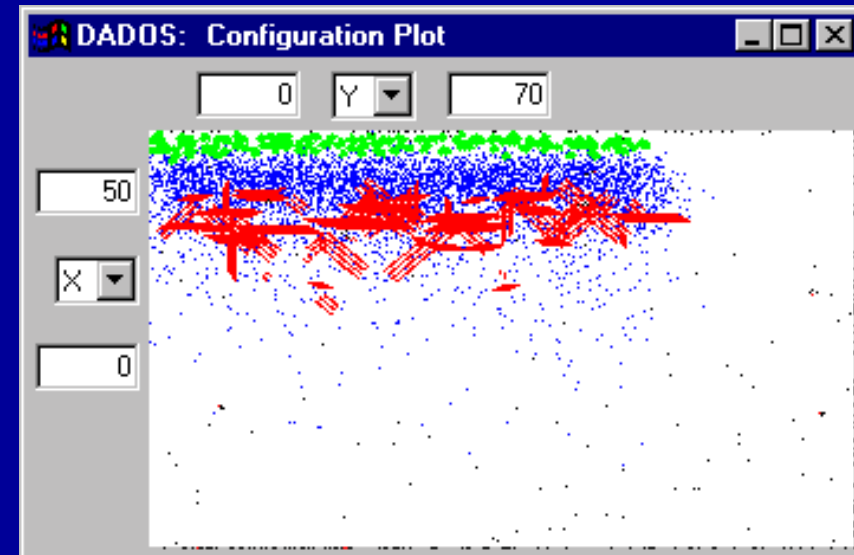


The Problem

Complex Materials Processing
Scenarios

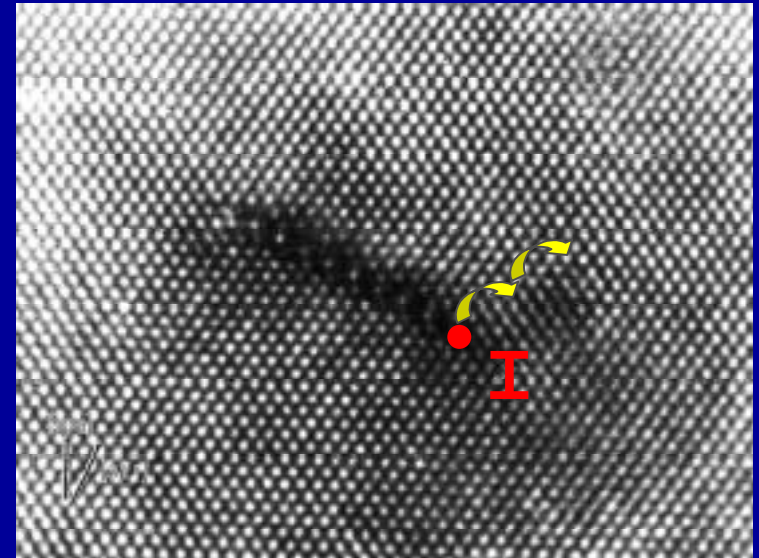
The Problem: Complex Processing Scenarios

1. Many different species (V, I, As, C, O, B, ...)
2. ... and interactions (I-B, V-O, I-C-O, ...)
3. Highly non-equilibrium conditions (Pair reactions, ...)
4. Extended defects (voids, {311}'s, loops, ...)
 - Emission/Capture rates dependent on Size & Shape
5. Low thermal budget (electrical activation?)
6. Ever smaller device dimensions
 - 2D: short channel effect
 - 3D: narrow channel effect
 - Local inhomogeneities (dopant discreteness)



The Problem: Complex Processing Scenarios

- Molecular Dynamics (MD) is most accurate, but limited to <1 nanosecond:
time step $\cong 10^{-15}$ s
- We use it (off-line) to calculate the KMC event rates.



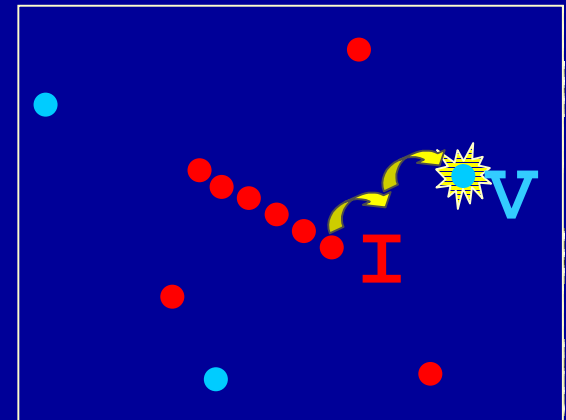


The Solution

Atomistic Kinetic Monte Carlo
(KMC)

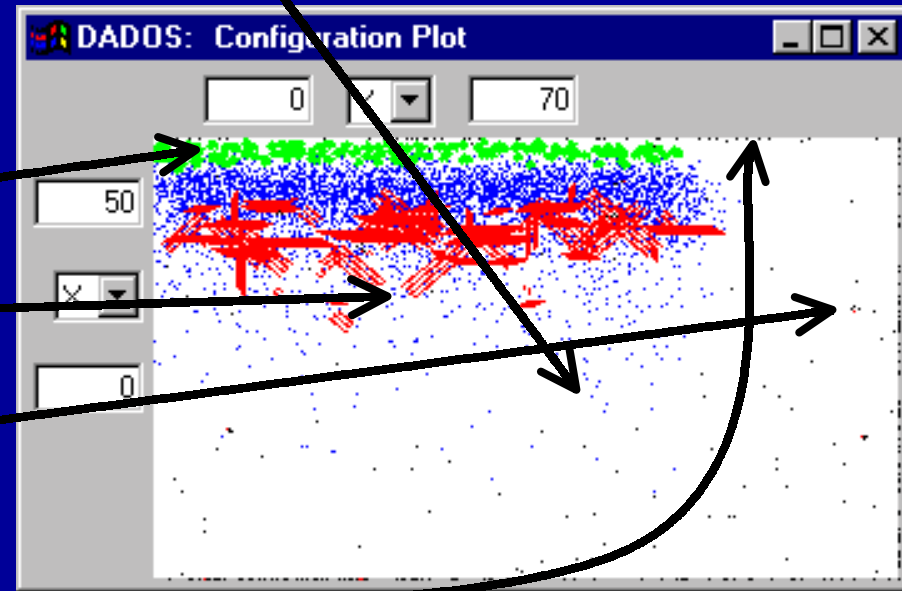
The Solution: Atomistic Kinetic Monte Carlo (KMC)

- KMC follows only the defect atoms
- Self-adjusts time step during the course of the simulation (Δt : $10^{-9} \rightarrow 10^3$ s)
- Uses event rates obtained from MD or experiments



Atomistic Modeling of Defects

- Point defects (V, I, B, As, ...)
- Extended defects (actual geometry)
 - Small clusters
 - V: Voids
 - I: {311}'s, Loops
 - Dopant clusters (B_nI_m, \dots)
- Surfaces



Defect Interactions

- Easy definition / modification :

...

```
case Vacancy:
    switch ( neighbor )
    {
        case Vacancy:
            return new Cluster<Vacancy>;
        case Bi:
            neighbor->delete();
            this->delete();
            return new PointD<Boron>;
    }
    ...
```

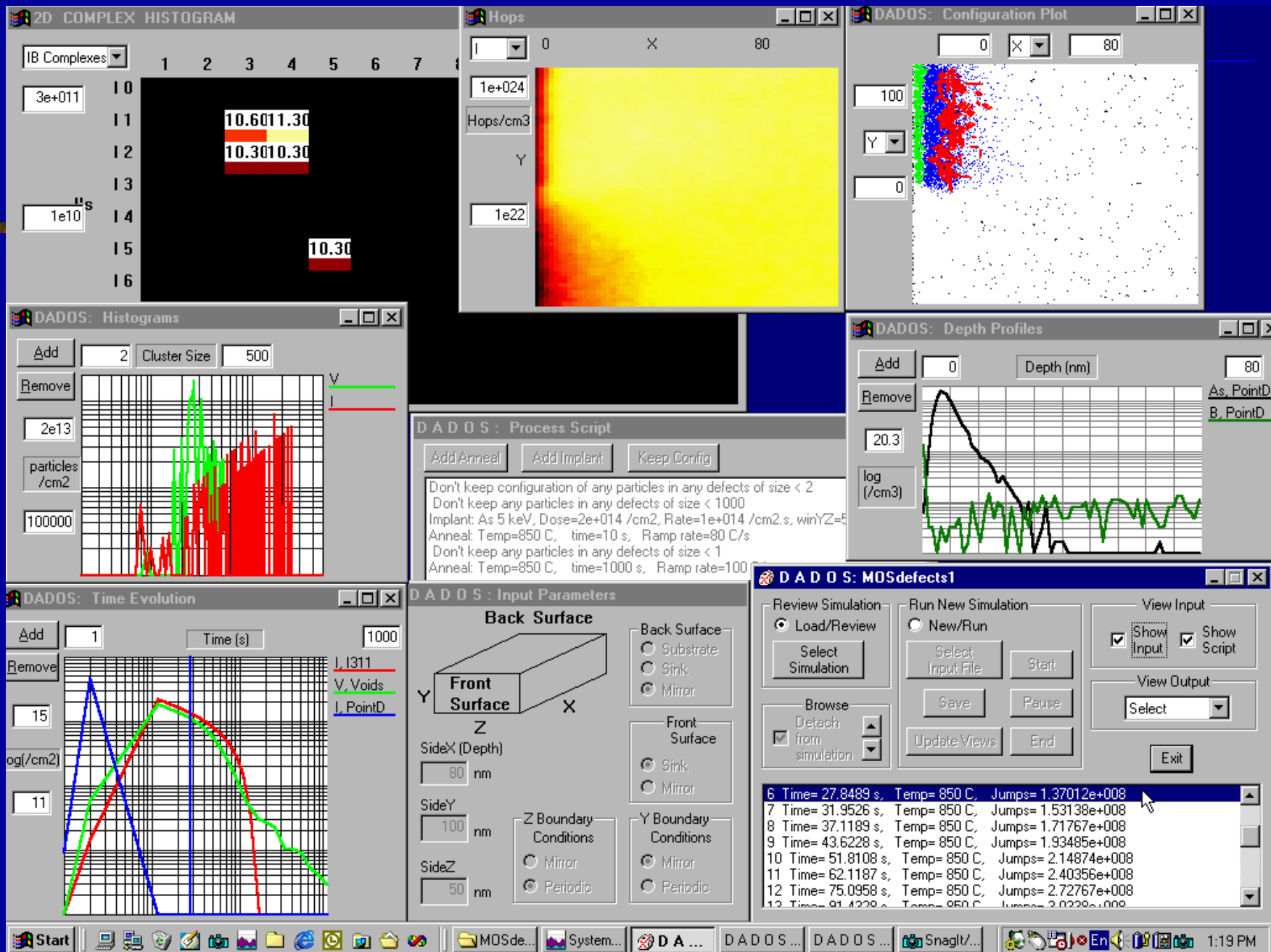
- Execution speed independent of number of interactions

The Event Scheduler

EXAMPLE:

	n	J_{rate} (jumps/s)	Total Jumps/s
V	2	1000	2000
I	5	10	50

- To simulate 1 second anneal we need to simulate 2050 Jumps
 $\Rightarrow \Delta t = 1/2050$ seconds per Jump
- We have to pick up V's and I's with a probability of 2000/2050 and 50/2050, respectively



KMC: Feature Example 1

Implantation Damage and the
“+N” Number

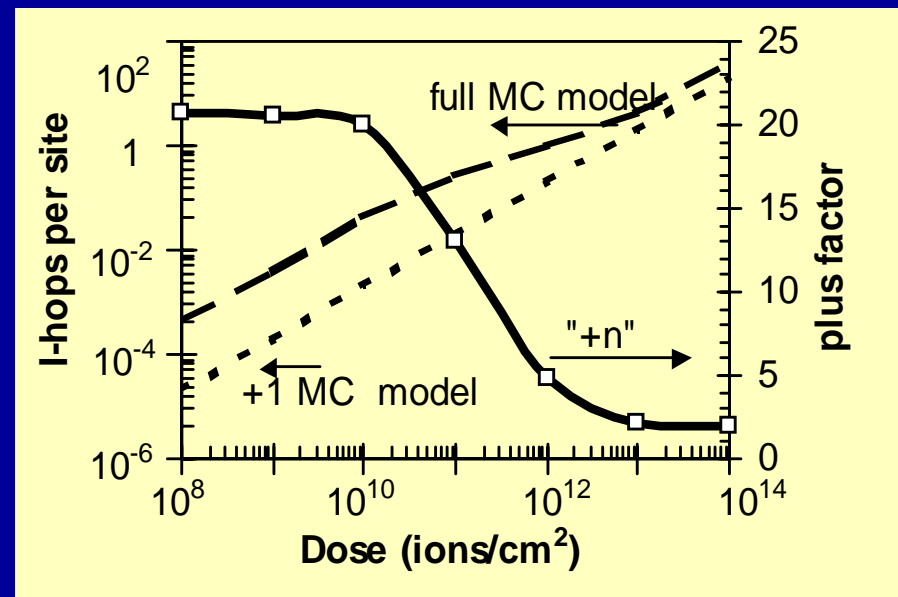
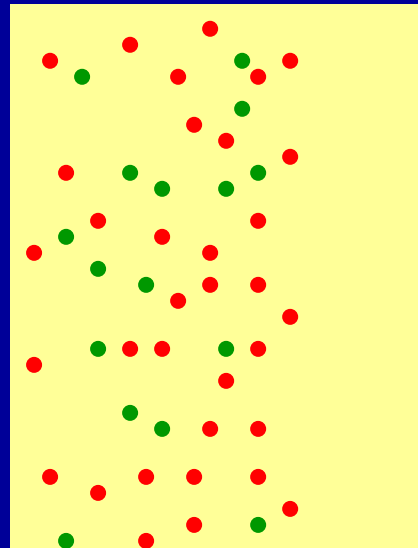
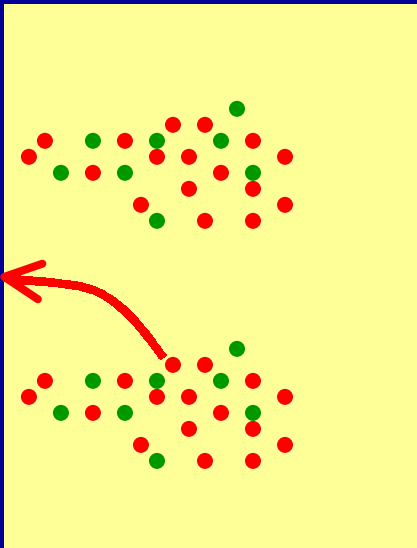
KMC can yield an accurate "+N" :

Low Dose Implant \rightarrow

Non-overlapping Cascades
(Spatial Inhomogeneities)

Atomistic

Continuum



Pelaz et al., APL. 74 (1999) 2017

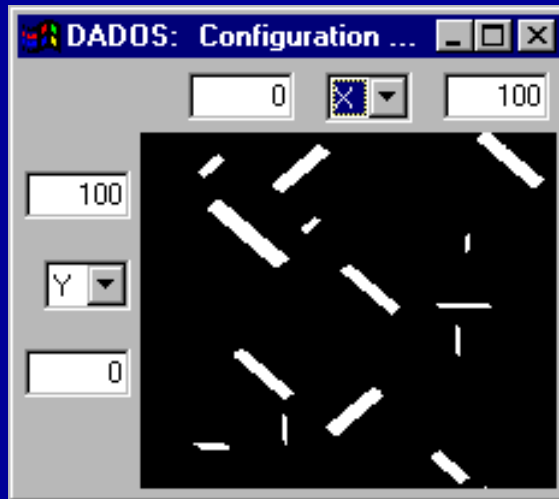


KMC: Feature Example 2

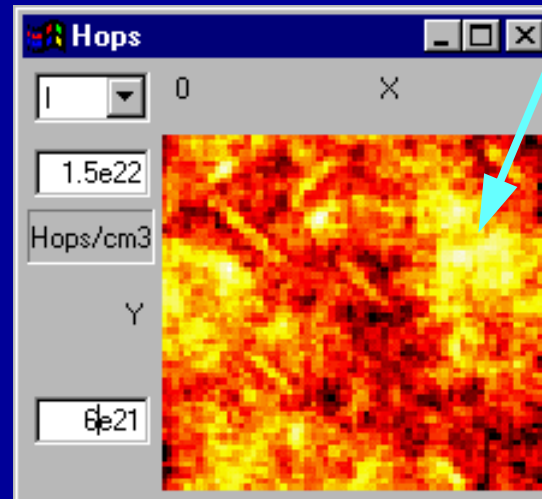
Local Inhomogeneities:

- Dopant Discreteness
- Clusters

Local Inhomogeneities: Clusters



{311} defects



Interst. hops

High B diffusivity

KMC: Feature Example 3

KMC used to validate
Simplifying Assumptions

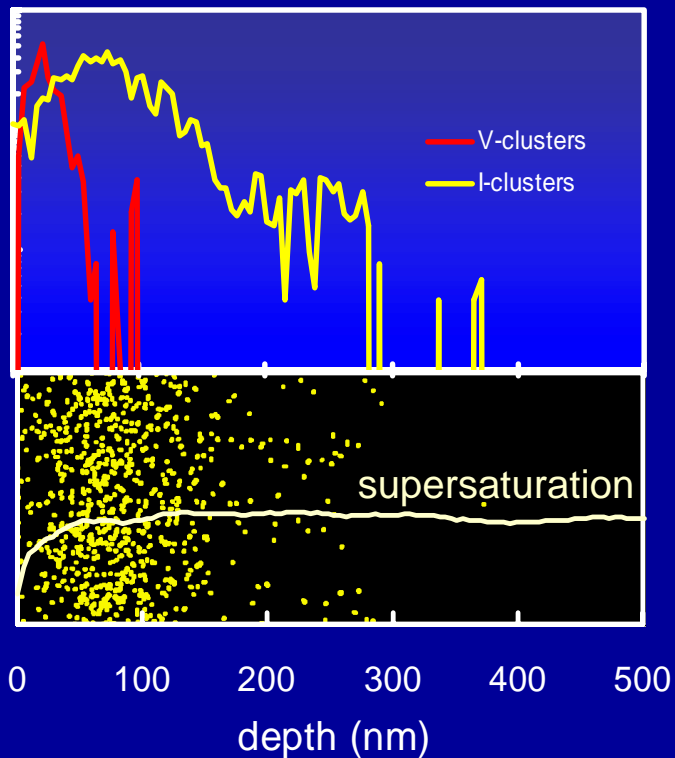
KMC used to validate simplifying assumptions

Emission energies of I-clusters:

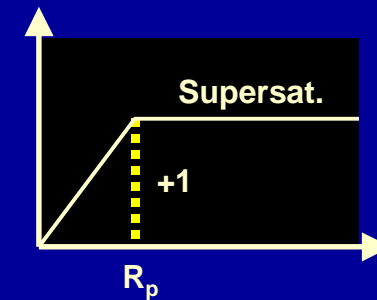
Cowern et al., *Phys. Rev. Lett.* **82**, 4460 (1999)

Implant + Anneal

600 °C, 1000 s



Simplified model



- No V's (" +1 " model)

- ...

$$\frac{dN_n}{dt} = F_{n-1}N_{n-1} - F_nN_n - R_nN_n + R_{n+1}N_{n+1}$$

$$S = \frac{\sum_{n=2}^{\infty} \beta_n R_n N_n}{D_I C_I^* (\sum_{n=2}^{\infty} 4\pi a_n N_n + 1/r_p)}$$

where

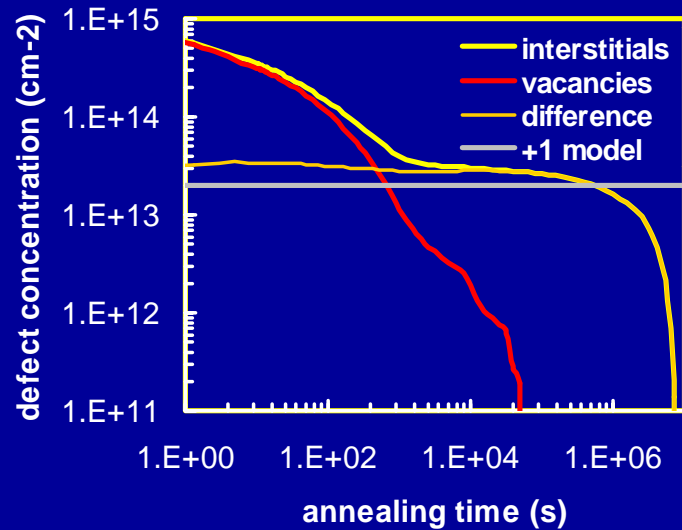
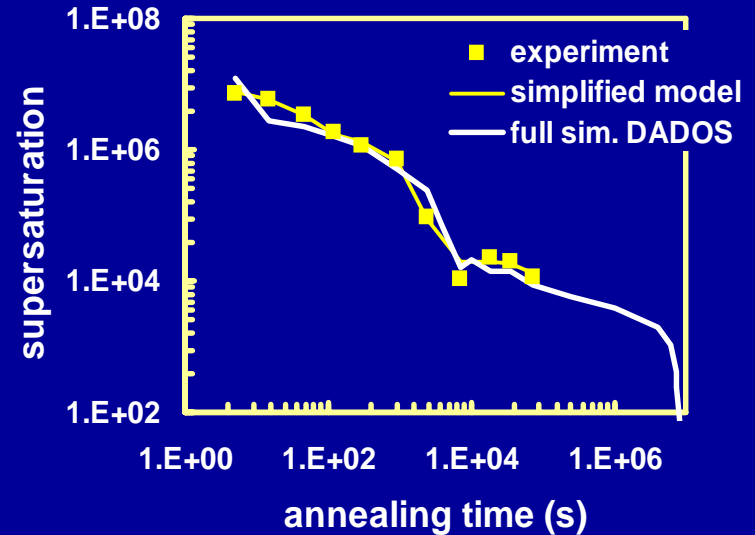
$$F_n = 4\pi a_n D_I C_I^* S,$$

$$R_n = (6D_{0n} a_n / \lambda^3) \exp -[E_{diss}(n)]/kT$$

How accurate is the Simplified model ?

- **Very good agreement with full simulation ...**

... in spite of the presence of Vacancies and other assumptions





The Challenge

Obtaining KMC Input Parameters
In Complex Scenarios

Evolutionary Computation (Genetic Algorithms, ...)

D. B. Fogel, IEEE Spectrum, Feb. 2000:

- “... is one of the fastest growing areas of Computer Science”
- “It is addressing **complex engineering** problems that were previously beyond reach”

Obtaining KMC Parameters from MD with a Genetic Algorithm

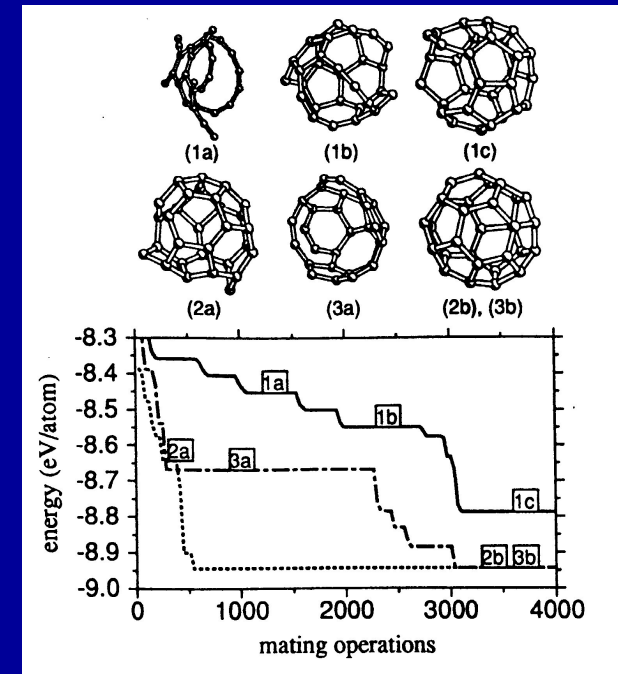
Problem: Find minimum energy configuration of 60 Carbon atoms, starting from random coordinates.

60 x 3 coords. = 180 unknowns

Assuming only 10 possible values for each coordinate: $\sim 10^{180}$ configs. ! (the Universe is about 10^{18} s old)

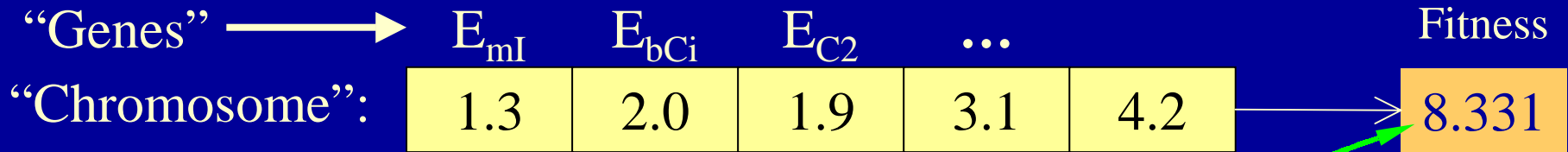
- The GA found the solution in ~ 5000 steps (configs.)
- It had not been solved by any other technique before

Free-standing Si clusters: Ho et al., *Nature* **392** (1998) 582

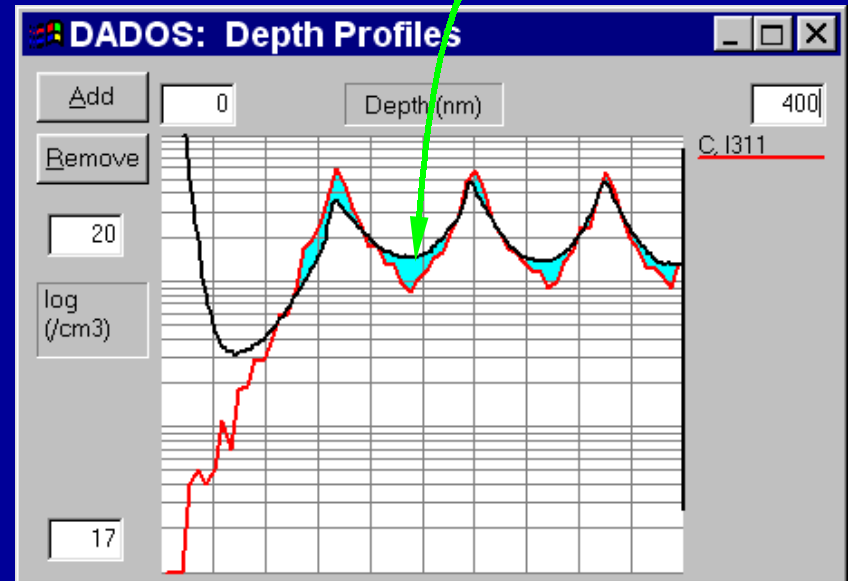
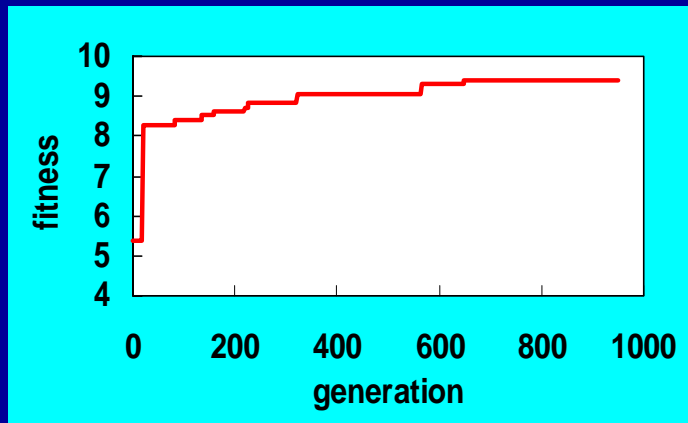


Deaven and Ho, PRL **75** (1995) 288

Using a GA To Extract KMC Parameters From Experimental Data

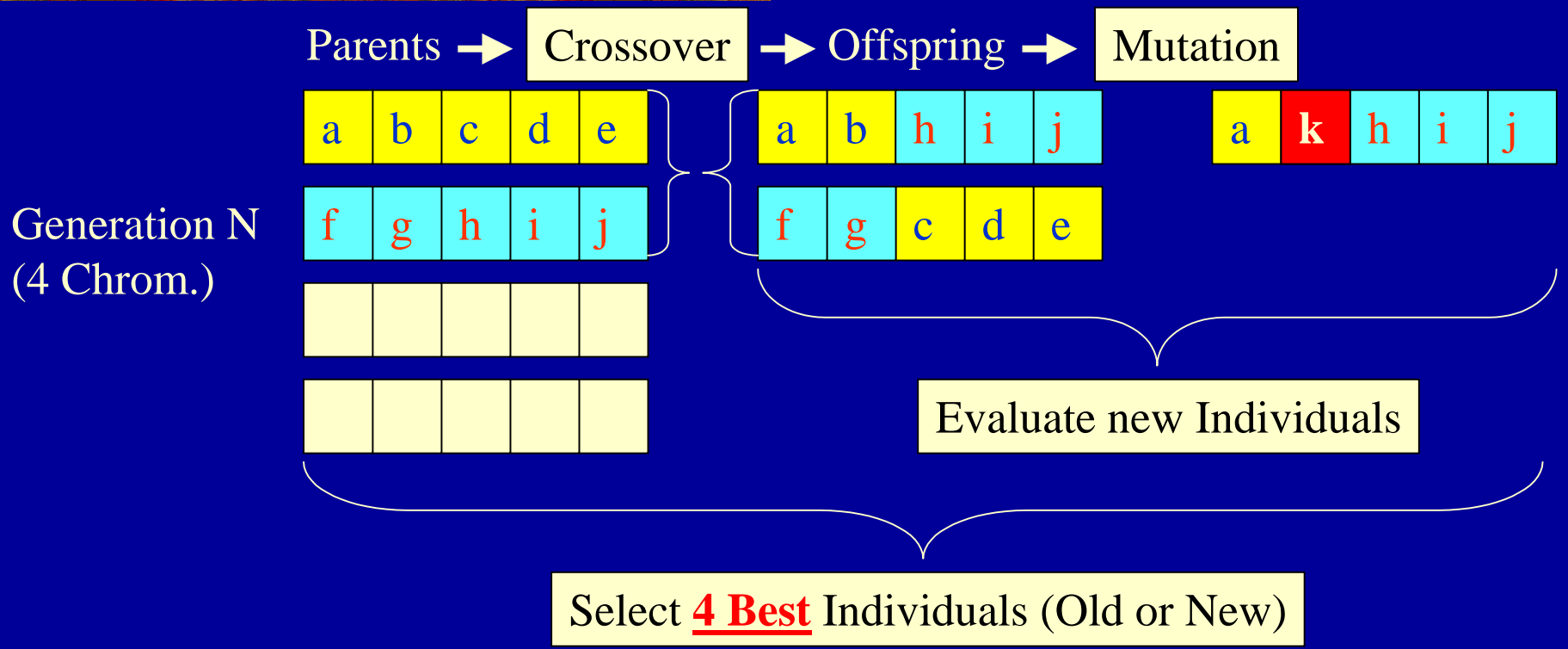


Fitness Evaluation: DADOS simulations
(just a rough estimate)
done in ~ 3 minutes / simulation



Genetic Algorithm from: <http://lancet.mit.edu/ga/>

What Is a Genetic Algorithm?

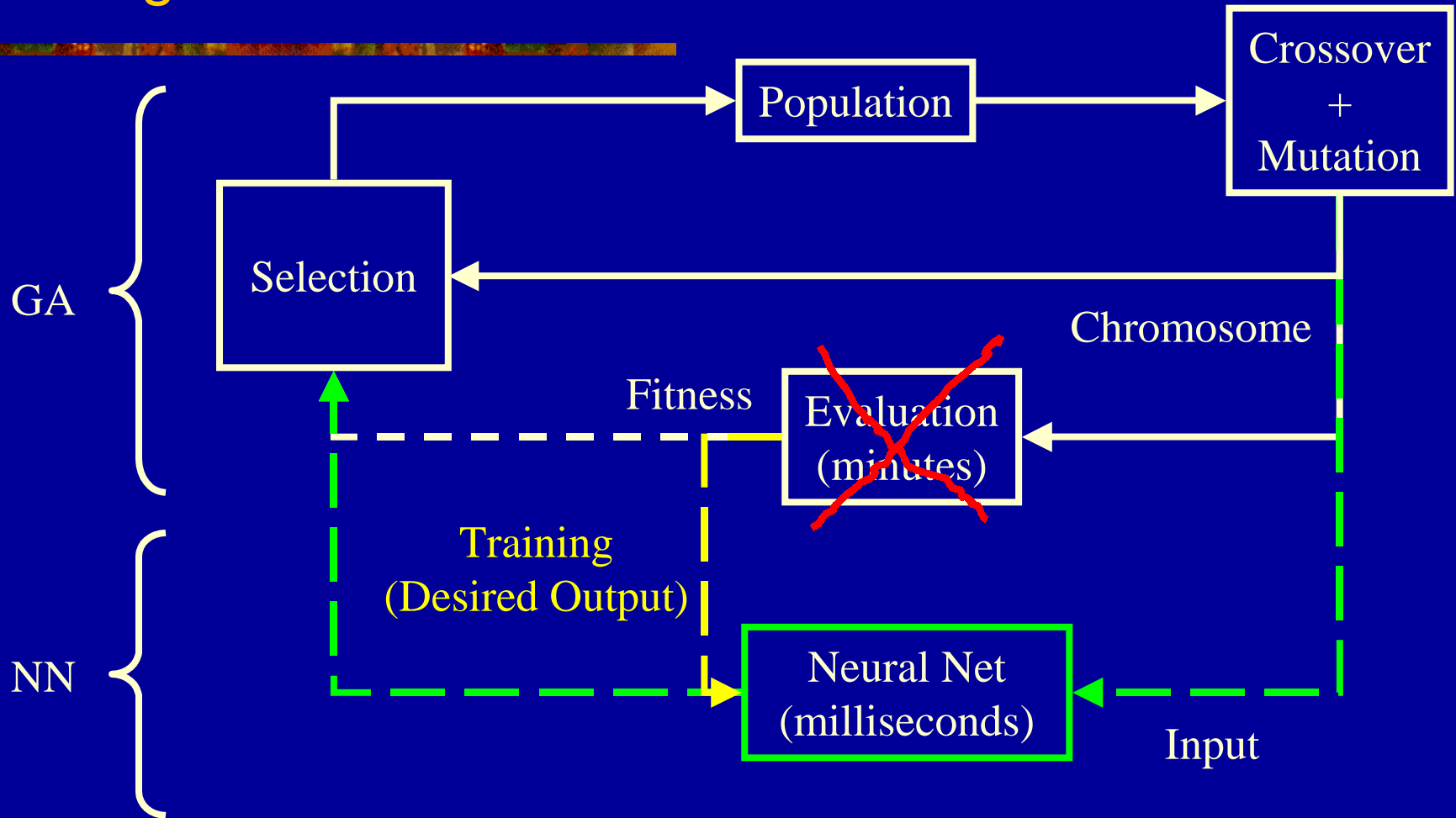


Generation N+1
(4 Chromosomes)



Looking Ahead

Looking Ahead: GA + Neural Networks



Looking Ahead

■ Genetic Programming

■ Symbolic Regression:

Set of symbols: { +, -, /, •, exp, cos, X, Y, Z, ... }

Find best fitting **function**: $f = X - Z \cdot \exp(Y)$

■ Materials Processing:

Set of mechanisms: { Frank-Turnbull,
Interstitialcy, Surface emission, E_1, E_2, \dots }

Find best mechanisms and energies

■ ...

In Summary:

Materials Research can benefit from:

- Atomistic KMC Process Modeling
 - Detailed and Accurate
 - Straightforward to Implement / Modify new Models
 - Can handle complex Processing scenarios
- AI methods (Genetic Algorithms, Neural Nets, ...)
 - Opening a whole new range of capabilities
 - Currently under intense exploration. Looks most promising

